

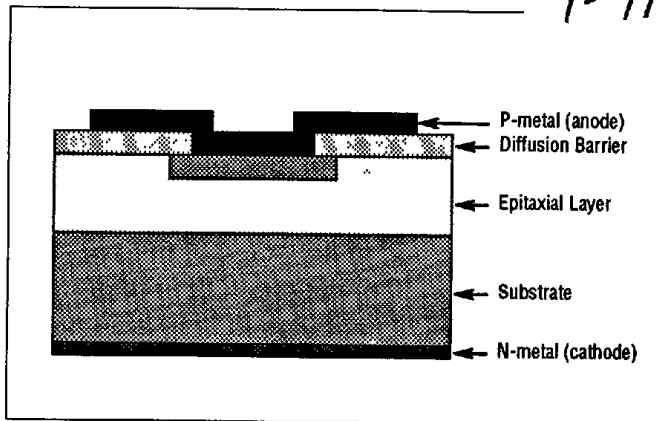
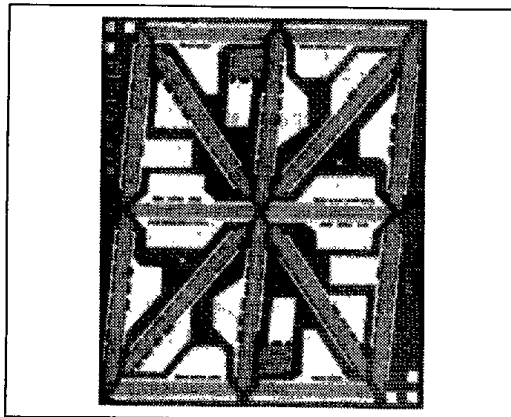
SIEMENS

**RM-81B
Mask-Diffused GaAsP
Monolithic LED**

Custom
Optoelectronic
Products

PART NO. 2680-0056

T-41-99



DESCRIPTION

Siemens RM-81B is a mask-diffused GaAsP monolithic light-emitting diode. With a bright and uniform 655 nm emission, this device is ideal for display applications.

MATERIAL

Epitaxial Layer: GaAs_{1-x}P_x : Te
 Substrate: GaAs : Si or GaAs : Te
 Metalizations: Anode Aluminum
 Cathode Gold-Germanium

Dimensions

(center to center): Height 0.135"
 Width 0.112"
 Thickness 0.010"

TYPICAL DEVICE PARAMETERS

Forward I-V Characteristics	V_{F3}	1.59 V	@ 20 mA
	V_{F2}	1.57 V	@ 10 mA
	V_{F1}	1.40 V	@ 100 μ A
Reverse I-V Characteristics	V_{R1}	-23.0 V	@ -10 μ A
Peak EL Wavelength	λ	655 nm	@ 20 mA
Spectral Half-Width	FWHM	40 nm	@ 20 mA
Luminous Intensity (Device does not have AR coating)	LI	220 μ Cd	@ 10 mA